

## EpiGaN expands GaN Power Production with AIX G5+ C

Leading European supplier of Gallium Nitride- (GaN-) based technology solutions relies on MOCVD production equipment from AIXTRON

**Herzogenrath/Germany, November 13, 2018** – AIXTRON SE (FSE: AIXA), a worldwide leading provider of deposition equipment to the semiconductor industry, today announced that EpiGaN has ordered an AIX G5+ C MOCVD system to boost its manufacturing capability of large diameter GaN-on-Si<sup>1</sup> and GaN-on-SiC<sup>2</sup> epiwafers. The Belgian company focuses on GaN-on-Si and GaN-on-SiC material product solutions for next-generation semiconductor devices for telecom, power electronics, and sensor applications.

The new AIXTRON AIX G5+ C reactor will be installed and operational in Q1/2019 at EpiGaN's manufacturing site in Hasselt/Belgium. The fully automated Planetary<sup>®</sup> MOCVD system features in-situ chamber cleaning and enables configurations of 8x6 inch or 5x8 inch epitaxial wafers to be automatically loaded and removed by a cassette-to-cassette wafer transfer module.

"The demand of our global customer base for GaN product solutions is boosting. Our key customers are getting ready to launch and scale-up products based on our GaN RF-power technology which is optimized for 5G broadband network applications. With AIXTRON's AIX G5+ C Planetary<sup>®</sup> system, EpiGaN will increase its capacity for 150mm and 200mm product solutions to scope the increasing market demand," says EpiGaN co-founder and CEO Dr. Marianne Germain. "AIXTRON's Planetary<sup>®</sup> system combines excellent on-wafer uniformity and run-to-run performance at the lowest cost of ownership – attributes that are critical to serve our customer base with products of exceptional performance and at the right price point."

Dr. Felix Grawert, President of AIXTRON, commented: "We are confident the AIX G5+ C will support EpiGaN's demanding requirements for high-quality, cost-effective production of GaN epitaxial wafers as our tool meets the highest standards in terms of uniformity and particle density."

Just recently EpiGaN has released large-diameter versions of its HVRF (High Voltage Radio Frequency) GaN-on-Si, as well as GaN-on-SiC wafer product families tailored towards demanding 5G applications needs. With the new AIX G5+ C MOCVD system from AIXTRON, EpiGaN expects to quickly scale up and spread out its differentiating technology solutions to the global market.

<sup>1</sup> GaN-on-Si = Gallium Nitride-on-Silicon, <sup>2</sup> GaN-on-SiC = Gallium Nitride-on-Silicon Carbide

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### For further information please contact

Corporate Communications  
AIXTRON SE, Dornkaulstr. 2, 52134 Herzogenrath, Germany  
PHONE +49 (2407) 9030-444 FAX +49 (2407) 9030-445  
E-MAIL [info@aixtron.com](mailto:info@aixtron.com) WEB [www.aixtron.com](http://www.aixtron.com)

## About AIXTRON

AIXTRON SE is a leading provider of deposition equipment to the semiconductor industry. The Company was founded in 1983 and is headquartered in Herzogenrath (near Aachen), Germany, with subsidiaries and sales offices in Asia, United States and in Europe. AIXTRON's technology solutions are used by a diverse range of customers worldwide to build advanced components for electronic and opto-electronic applications based on compound, or organic semiconductor materials. Such components are used in a broad range of innovative applications, technologies and industries. These include LED applications, display technologies, data transmission, SiC and GaN power management and conversion, communication, signaling and lighting as well as a range of other leading-edge technologies.

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For further information on AIXTRON (FSE: AIXA, ISIN DE000A0WMPJ6) please visit our website at: [www.aixtron.com](http://www.aixtron.com).

## About EpiGaN

Founded in 2010 EpiGaN provides innovative GaN technology solutions to its global customer base. From its European headquarters and modern production site in Hasselt/Belgium the company offers early access to leading-edge GaN/Si and GaN/SiC epiwafer technology for next-generation power switching, RF power, and advanced sensor solutions. EpiGaN's GaN technology is a key enabler for device innovation in consumer power supplies, electric vehicles, wireless charging and RF power systems for next-generation cellular infrastructures – 5G, IoT (Internet of Things), and smart sensor systems. The product spectrum ranges from application-specific standard epi-wafers of up to 200mm diameter to customized products utilizing the company's differentiating technology of AlN barrier and in-situ SiN passivation layers.

For further information on EpiGaN nv, please visit our website at: [www.epigan.com](http://www.epigan.com).

## Forward-Looking Statements

This document may contain forward-looking statements regarding the business, results of operations, financial condition and earnings outlook of AIXTRON. These statements may be identified by words such as "may", "will", "expect", "anticipate", "contemplate", "intend", "plan", "believe", "continue" and "estimate" and variations of such words or similar expressions. These forward-looking statements are based on our current assessments, expectations and assumptions, of which many are beyond control of AIXTRON, and are subject to risks and uncertainties. You should not place undue reliance on these forward-looking statements. Should these risks or uncertainties materialize, or should underlying expectations not occur or assumptions prove incorrect, actual results, performance or achievements of AIXTRON may materially vary from those described explicitly or implicitly in the relevant forward-looking statement. This could result from a variety of factors, such as actual customer orders received by AIXTRON, the level of demand for deposition technology in the market, the timing of final acceptance of products by customers, the condition of financial markets and access to financing for AIXTRON, general conditions in the market for deposition plants and macroeconomic conditions, cancellations, rescheduling or delays in product shipments, production capacity constraints, extended sales and qualification cycles, difficulties in the production process, the general development in the semi-conductor industry, increased competition, fluctuations in exchange rates, availability of public funding, fluctuations and/or changes in interest rates, delays in developing and marketing new products, a deterioration of the general economic situation and any other factors discussed in any reports or other announcements, in particular in the chapter Risks in the Annual Report, filed by AIXTRON. Any forward-looking statements contained in this document are based on current expectations and projections of the executive board based on information available the date hereof. AIXTRON undertakes no obligation to revise or update any forward-looking statements as a result of new information, future events or otherwise, unless expressly required to do so by law.

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## For further information please contact

Corporate Communications

AIXTRON SE, Dornkaulstr. 2, 52134 Herzogenrath, Germany

PHONE +49 (2407) 9030-444 FAX +49 (2407) 9030-445

E-MAIL [info@aixtron.com](mailto:info@aixtron.com) WEB [www.aixtron.com](http://www.aixtron.com)